

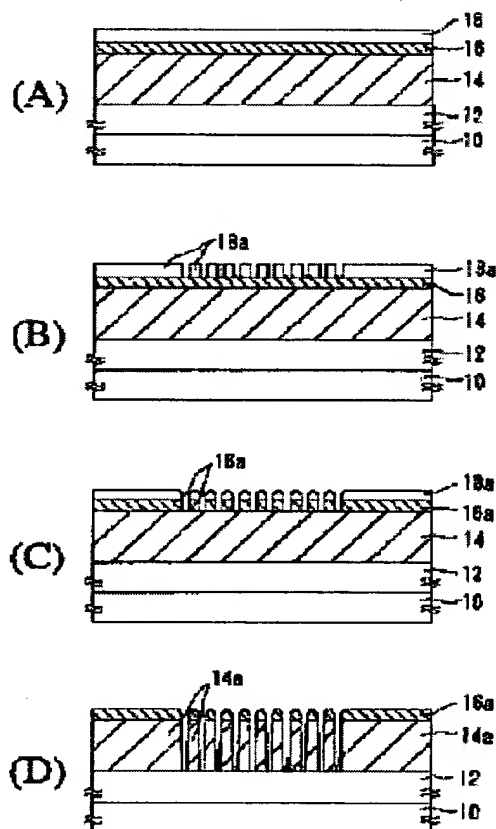
**FORMATION OF PATTERN**

**Patent number:** JP8083756  
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**Inventor:** NODA SHUICHI  
**Applicant:** OKI ELECTRIC IND CO LTD  
**Classification:**  
- **International:** C23F1/12; H01L21/027; H01L21/3065; C23F1/10; H01L21/02; (IPC1-7): H01L21/027; C23F1/12; H01L21/3065  
- **European:**  
**Application number:** JP19940219740 19940914  
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**Abstract of JP8083756**

**PURPOSE:** To easily form a pattern with high accuracy by performing reactive ion etching (RIE) by using a mask pattern made of titanium(Ti) as an etching mask and a mixed gas of chlorine gas (Cl<sub>2</sub>) and oxygen gas (O<sub>2</sub>) as a reactive gas. **CONSTITUTION:** A sample substrate is prepared by successively forming a silicon nitride (SiN<sub>x</sub>) film 12, tungsten (W) film 14 formed as a layer to be etched, titanium(Ti) film 16, and EB resist film 18 on a silicon substrate 10. Firstly, a resist pattern 18a is formed on the titanium film 16 and RIE is performed on the film 16 by using the resist pattern 18a. As a result of the etching, a Ti mask pattern 16a is formed. Then an X-ray absorber pattern 14a is formed by performing RIE on the layer (W film) 14 to be etched by using the mask pattern 16a as an etching mask and a mixed gas of chlorine gas (Cl<sub>2</sub>) and oxygen gas (O<sub>2</sub>) as a reaction gas.



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